

BG100G12F13L4

□ General Description

BYD IGBT Power Module BG100G12F13L4 provides low switching losses characteristic as well as high power and thermal cycling capability, which introduce the advanced IGBT chip/FRD and improved connection.



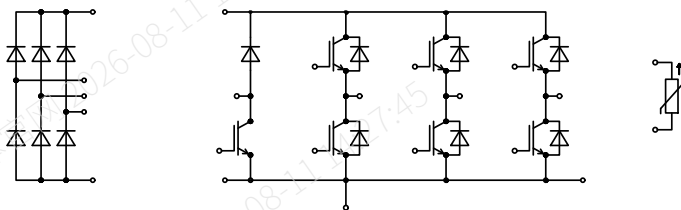
□ 概述

BYD IGBT 功率模块 BG100G12F13L4 采用高性能的 IGBT 芯片和 FRD 芯片和优化的电气连接，具有低开关损耗和高功率循环和温度循环能力。

$V_{CES}=1200V$, $I_c=100A$

□ Key Features

- 1200V planar field-stop technology
- Low conduction and switching losses
- V_{CESat} with positive temperature coefficient
- Low V_{CESat}



□ 关键特性

- 1200V 平面栅场终止技术
- 低导通和开关损耗
- V_{CESat} 正温度系数
- 低 V_{CESat}

□ Applications

- Auxiliary Inverters
- Servo drives
- Motor drives

□ 应用

- 辅助逆变器
- 伺服驱动器
- 电机传动

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IGBT, 逆变器/ IGBT, Inverter

● Maximum Rated Values/最大额定值

符号 Symbol	参数 Parameter	工作条件 Conditions	额定值 Ratings	单位 Units
V_{CES}	Collector-emitter voltage 集电极-发射极电压	$T_{vj}=25^{\circ}\text{C}$	1200	V
I_C	Collector current 连续集电极直流电流	$T_C=100^{\circ}\text{C}$, $T_{vj\max}=175^{\circ}\text{C}$	100	A
V_{GES}	Gate-emitter voltage 栅极-发射极峰值电压		± 20	V
I_{CRM}	Repetitive peak collector current 集电极重复峰值电流	$t_p=1\text{ms}$	200	A
P_{tot}	Total power dissipation 总功率损耗	$T_C=25^{\circ}\text{C}$, $T_{vj\max}=175^{\circ}\text{C}$	515	W

● Characteristics Values/特征值

符号 Symbol	参数 Parameter	工作条件 Conditions		额定值 Ratings			单位 Units
				Min.	Typ.	Max.	
V _{CE sat}	Collector-Emitter Saturation Voltage 集电极-发射极饱和电压	I _C =100A, V _{GE} =15V, T _{vj} =25℃	-	2.4	2.7	V	
		I _C =100A, V _{GE} =15V, T _{vj} =125℃	-	2.55	-	V	
		I _C =100A, V _{GE} =15V, T _{vj} =150℃	-	2.6	-	V	
V _{GEth}	Gate threshold voltage 栅极阈值电压	V _{CE} =V _{GE} , I _C =4mA, T _{vj} =25℃	5.0	5.9	7.0	V	
Q _G	Gate charge 栅极电荷	V _{GE} =-8V...+15V	-	0.25	-	uC	
R _{Gint}	Internal gate resistance 内部栅极电阻	T _{vj} =25℃	-	12	-	Ω	
C _{ies}	Input capacitance 输入电容	T _{vj} =25℃, f=1MHz, V _{GE} =0V, V _{CE} =25V	-	4.52	-	nF	
C _{res}	Reverse capacitance 反向传输电容		-	0.23	-	nF	
I _{CES}	Collector-emitter cut-off current 集电极-发射极截止电流	V _{CE} =1200V, V _{GE} =0V, T _{vj} =25℃	-	-	1.0	mA	
I _{GES}	Gate-emitter leakage current 栅极-发射极漏电流	V _{CE} =0V, V _{GE} =20V, T _{vj} =25℃	-	-	200	nA	
t _{d on}	Turn-on delay time 开通延迟时间	I _C = 100A, V _{CE} = 600 V, V _{GE} =-8V...+15V, R _{Gon} / R _{Goff} = 2Ω/13.5Ω	T _{vj} =25℃	-	95	-	ns
			T _{vj} =125℃	-	95	-	ns
			T _{vj} =150℃	-	97	-	ns

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t_r	Rise time 上升时间		$T_{vj}=25^{\circ}\text{C}$	-	87	-	ns	
			$T_{vj}=125^{\circ}\text{C}$	-	87	-	ns	
			$T_{vj}=150^{\circ}\text{C}$	-	89	-	ns	
$t_{d\text{ off}}$	Turn-off delay time 关断延迟时间		$T_{vj}=25^{\circ}\text{C}$	-	409	-	ns	
			$T_{vj}=125^{\circ}\text{C}$	-	469	-	ns	
			$T_{vj}=150^{\circ}\text{C}$	-	487	-	ns	
t_f	Fall time 下降时间		$T_{vj}=25^{\circ}\text{C}$	-	29	-	ns	
			$T_{vj}=125^{\circ}\text{C}$	-	216	-	ns	
			$T_{vj}=150^{\circ}\text{C}$	-	225	-	ns	
E_{on}	Turn-on energy loss 开通损耗能量		$T_{vj}=25^{\circ}\text{C}$	-	9.7	-	mJ	
			$T_{vj}=125^{\circ}\text{C}$	-	11.6	-	mJ	
			$T_{vj}=150^{\circ}\text{C}$	-	12.5	-	mJ	
E_{off}	Turn-off energy loss 关断损耗能量		$T_{vj}=25^{\circ}\text{C}$	-	5.4	-	mJ	
			$T_{vj}=125^{\circ}\text{C}$	-	9.9	-	mJ	
			$T_{vj}=150^{\circ}\text{C}$	-	10.7	-	mJ	
t_{sc}	Short Circuit Withstand Time 短路耐受时间	$V_{\text{GE}}\leq 15\text{V}$, $V_{\text{cc}}=800\text{V}$, $V_{\text{CE max}} = V_{\text{CES}} - L_{\text{sCE}} \cdot di/dt$	$T_{vj}=25^{\circ}\text{C}$	-	10	-	us	
R_{thJC}	Thermal resistance, junction to case 结—外壳热阻	per IGBT/每个 IGBT		-	-	0.29	K/W	
R_{thCH}	Thermal resistance, case to heatsink 外壳—散热器热阻	per IGBT/每个 IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ $/ \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		-	0.12	-	K/W	
$T_{vj\text{ op}}$	Temperature under switching conditions 在开关状态下温度			-40	-	150	$^{\circ}\text{C}$	

□ FRD, 逆变器/ Diode, Inverter

● Maximum Rated Values/最大额定值

符号 Symbol	参数 Parameter	工作条件 Conditions	额定值 Ratings	单位 Units
V_{RRM}	Repetitive peak reverse voltage 反向重复峰值电压	$T_{vj} = 25^{\circ}\text{C}$	1200	V
I_F	Forward current of diode 连续正向直流电流		100	A
I_{FRM}	Repetitive peak forward current 正向重复峰值电流	$t_p = 1\text{ms}$	200	A
I^2t	I^2t – value I^2t -值	$V_R = 0\text{ V}$, $t_p = 10\text{ ms}$, $T_{vj} = 125^{\circ}\text{C}$	1800	A^2S

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● Characteristics Values/特征值

符号 Symbol	参数 Parameter	工作条件 Conditions		额定值 Ratings			单位 Units
				Min.	Typ.	Max.	
V _F	Forward voltage 正向电压	I _F =100A, V _{GE} =0V	T _{vj} =25℃	1.70	2.15	2.60	V
			T _{vj} =125℃	-	2.1	-	V
			T _{vj} =150℃	-	2.05	-	V
I _{RM}	Peak reverse recovery current 反向恢复峰值电流	I _F = 100A, - di _F /dt = 1100 A/μs (T _{vj} =150℃) V _R = 600 V V _{GE} = -8 V	T _{vj} =25℃	-	48	-	A
			T _{vj} =125℃	-	55	-	A
			T _{vj} =150℃	-	57	-	A
Q _r	Recovered charge 恢复电荷		T _{vj} =25℃	-	5.4	-	uC
			T _{vj} =125℃	-	12	-	uC
			T _{vj} =150℃	-	14.3	-	uC
E _{rec}	Reverse recovery energy 反向恢复损耗		T _{vj} =25℃	-	2	-	mJ
			T _{vj} =125℃	-	4.8	-	mJ
			T _{vj} =150℃	-	5.9	-	mJ
R _{thJC}	Thermal resistance, junction to case 结—外壳热阻	per diode /每个二极管		-	-	0.25	K/W
R _{thCH}	Thermal resistance, case to heatsink 外壳—散热器热阻	per diode /每个二极管 λ _{Paste} = 1W/(m·K) / λ _{grease} = 1W/(m·K)		-	0.22	-	K/W
T _{vj op}	Temperature under switching conditions 在开关状态下温度			-40	-	150	℃

□ FRD, 整流管/ Diode, Rectifier

● Maximum Rated Values/最大额定值

符号 Symbol	参数 Parameter	工作条件 Conditions	额定值 Ratings	单位 Units
V_{RRM}	Repetitive peak reverse voltage 反向重复峰值电压	$T_{vj} = 25^{\circ}C$	1600	V
I_{FRMSM}	Maximum RMS forward current per chip 最大正向均方根电流 (每芯片)	$T_C = 85^{\circ}C$	100	A
I_{RMSM}	Maximum RMS current at rectifier output 最大整流器输出均方根电流	$T_C = 85^{\circ}C$	120	A
I_{FSM}	Repetitive peak forward current 正向浪涌电流	$t_p=10ms, T_{vj} = 25^{\circ}C$	840	A
		$t_p=10ms, T_{vj} = 150^{\circ}C$	730	A
I^2t	I^2t – value I^2t -值	$t_p = 10 ms, T_{vj} = 25^{\circ}C$	3500	A^2S
		$t_p = 10 ms, T_{vj} = 150^{\circ}C$	2600	A^2S

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● Characteristics Values/特征值

符号 Symbol	参数 Parameter	工作条件 Conditions		额定值 Ratings			单位 Units
				Min.	Typ.	Max.	
V_F	Forward voltage 正向电压	$I_F=100A$	$T_{vj}=150^{\circ}C$	-	1.14	-	V
I_R	Reverse current 反向电流	$V_R=1600V$	$T_{vj}=25^{\circ}C$	-	10	-	uA
			$T_{vj}=150^{\circ}C$	-	2	-	mA
R_{thJC}	Thermal resistance, junction to case 结-外壳热阻	per diode /每个二极管		-	-	0.55	K/W
R_{thCH}	Thermal resistance, case to heatsink 外壳-散热器热阻	per diode /每个二极管 $\lambda_{Paste} = 1W/(m \cdot K)$ / $\lambda_{grease} = 1W/(m \cdot K)$		-	0.25	-	K/W
$T_{vj op}$	Temperature under switching conditions 在开关状态下温度			-40	-	150	$^{\circ}C$

□ IGBT, 制动-斩波器/IGBT, Brake-Chopper

● Maximum Rated Values/最大额定值

符号 Symbol	参数 Parameter	工作条件 Conditions	额定值 Ratings	单位 Units
V_{CES}	Collector-emitter voltage 集电极-发射极电压	$T_{vj}=25^{\circ}C$	1200	V
I_C	Collector current 连续集电极直流电流	$T_c=100^{\circ}C$, $T_{vj max}=175^{\circ}C$	50	A
V_{GES}	Gate-emitter voltage 栅极-发射极峰值电压		± 20	V
P_{tot}	Total power dissipation 总功率损耗	$T_c=25^{\circ}C$, $T_{vj max}=175^{\circ}C$	280	W

● Characteristics Values/特征值

符号 Symbol	参数 Parameter	工作条件 Conditions	额定值 Ratings			单位 Units
			Min.	Typ.	Max.	
V_{CEsat}	Collector-Emitter Saturation Voltage 集电极-发射极饱和电压	$I_C=50A, V_{GE}=15V, T_{vj}=25^{\circ}C$	-	2.25	2.50	V
		$I_C=50A, V_{GE}=15V, T_{vj}=125^{\circ}C$	-	2.39	-	V
		$I_C=50A, V_{GE}=15V, T_{vj}=150^{\circ}C$	-	2.50	-	V
V_{GEth}	Gate threshold voltage 栅极阈值电压	$V_{CE}=V_{GE}, I_C=2mA, T_{vj}=25^{\circ}C$	5.0	6.0	7.0	V

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Q _G	Gate charge 栅极电荷	V _{GE} =-8V...+15V		-	0.15	-	uC
R _{Gint}	Internal gate resistance 内部栅极电阻	T _{vj} =25℃		-	12	-	Ω
C _{ies}	Input capacitance 输入电容	T _{vj} =25℃,f=1MHz, V _{GE} =0V, V _{CE} =25V		-	2.2	-	nF
C _{res}	Reverse capacitance 反向传输电容			-	0.18	-	nF
I _{CES}	Collector-emitter cut-off current 集电极-发射极截止电流	V _{CE} =1200V,V _{GE} =0V,T _{vj} =25℃		-	-	1.0	mA
I _{GES}	Gate-emitter leakage current 栅极-发射极漏电流	V _{CE} =0V,V _{GE} =20V,T _{vj} =25℃		-	-	200	nA
t _{d on}	Turn-on delay time 开通延迟时间	I _C = 50A, V _{CE} = 600 V, V _{GE} =-8V...+15V, R _{Gon} = R _{Goff} = 13Ω	T _{vj} =25℃	-	80	-	ns
			T _{vj} =125℃	-	85	-	ns
			T _{vj} =150℃	-	90	-	ns
t _r	Rise time 上升时间		T _{vj} =25℃	-	50	-	ns
			T _{vj} =125℃	-	55	-	ns
			T _{vj} =150℃	-	60	-	ns
t _{d off}	Turn-off delay time 关断延迟时间		T _{vj} =25℃	-	198	-	ns
			T _{vj} =125℃	-	237	-	ns
			T _{vj} =150℃	-	246	-	ns
t _f	Fall time 下降时间		T _{vj} =25℃	-	98	-	ns
			T _{vj} =125℃	-	194	-	ns
			T _{vj} =150℃	-	225	-	ns
E _{on}	Turn-on energy loss 开通损耗能量		T _{vj} =25℃	-	4.0	-	mJ
			T _{vj} =125℃	-	6.1	-	mJ
			T _{vj} =150℃	-	6.7	-	mJ
E _{off}	Turn-off energy loss 关断损耗能量		T _{vj} =25℃	-	2.2	-	mJ
			T _{vj} =125℃	-	3.8	-	mJ
			T _{vj} =150℃	-	4.3	-	mJ
t _{sc}	Short Circuit Withstand Time 短路耐受时间	V _{GE} ≤15V, V _{cc} =800V, V _{CE max} = V _{CES} -L _{sCE} ·di/dt	T _{vj} =25℃	-	10	-	us
R _{thJC}	Thermal resistance, junction to case 结—外壳热阻	per IGBT /每个 IGBT		-	-	0.54	K/W
R _{thCH}	Thermal resistance, case to heatsink 外壳—散热器热阻	per IGBT /每个 IGBT λ _{Paste} = 1 W/(m·K) / λ _{grease} = 1 W/(m·K)		-	0.26	-	K/W

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$T_{vj\ op}$	Temperature under switching conditions 在开关状态下温度			-40	-	150	°C
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□ FRD, 制动-斩波器/Diode, Brake-Chopper

● Maximum Rated Values/最大额定值

符号 Symbol	参数 Parameter	工作条件 Conditions	额定值 Ratings	单位 Units
V_{RRM}	Repetitive peak reverse voltage 反向重复峰值电压	$T_{vj} = 80^{\circ}\text{C}$	1200	V
I_F	Forward current of diode 连续正向直流电流		25	A
I_{FRM}	Repetitive peak forward current 正向重复峰值电流	$t_p = 1\text{ms}$	50	A
I^2t	I^2t - value I^2t -值	$V_R = 0\text{ V}$, $t_p = 10\text{ ms}$, $T_{vj} = 125^{\circ}\text{C}$	150	A ² S

● Characteristics Values/特征值

符号 Symbol	参数 Parameter	工作条件 Conditions		额定值 Ratings			单位 Units	
				Min.	Typ.	Max.		
V _F	Forward voltage 正向电压	I _F =25A, V _{GE} =0V	T _{vj} =25℃	1.60	1.86	2.50	V	
			T _{vj} =150℃	-	1.82	-	V	
I _{RM}	Peak reverse recovery current 反向恢复峰值电流	I _F = 25 A, - di _F /dt = 500 A/μs (T _{vj} =150℃) V _R = 600 V	T _{vj} =25℃	-	17	-	A	
			T _{vj} =150℃	-	21	-	A	
Q _r	Recovered charge 恢复电荷		T _{vj} =25℃	-	2.1	-	uC	
			T _{vj} =150℃	-	4.4	-	uC	
E _{rec}	Reverse recovery energy 反向恢复损耗		T _{vj} =25℃	-	0.5	-	mJ	
			T _{vj} =150℃	-	1.5	-	mJ	
R _{thJC}	Thermal resistance, junction to case 结－外壳热阻	per diode /每个二极管		-	-	1.2	K/W	
R _{thCH}	Thermal resistance, case to heatsink 外壳－散热器热阻	per diode /每个二极管 λ _{Paste} = 1W/(m·K) / λ _{grease} = 1W/(m·K)		-	0.02	-	K/W	
T _{vj op}	Temperature under switching conditions 在开关状态下温度			-40	-	150	℃	

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□ NTC-Thermistor/负温度系数热敏电阻

参数 Parameter	符号 Symbol	工作条件 Conditions	额定值 Ratings			单位 Units
			Min.	Typ.	Max.	
Rated resistance 额定电阻值	R ₂₅	T _C =25℃	-	5.0	-	kΩ
Deviation of R100 R100 偏差	ΔR/R	T _C =100℃, R ₁₀₀ =493Ω	-5	-	5	%
Power dissipation 耗散功率	P ₂₅	T _C =25℃	-	-	20	mW
B-value/B-值	B _{25/50}	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$	-	3375	-	K
B-value/ B-值	B _{25/80}	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15K))]$	-	3411	-	K
B-value/ B-值	B _{25/100}	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15K))]$	-	3433	-	K

□ Module/模块

符号 Symbol	参数 Parameter	工作条件 Conditions	额定值 Ratings			单位 Units
			Min.	Typ.	Max.	
T _{vj max}	Maximum junction temperature 最大结温	inverter,brake-chopper /逆变器，制动-斩波器	175			℃
		Rectifier /整流器	150			
T _{vj op}	Temperature under switching conditions 工作结温	-	-40	-	150	℃
T _{stg}	Storage temperature 储存温度	-	-40	-	125	℃
CT1	Comparative tracking index 相对电痕指数	-	-	>200	-	-
R _{thCH}	Thermal resistance, Case to heatsink 外壳-散热器热阻	每个模块 / per module $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$	-	0.01	-	K/W
L _{sCE}	Stray inductance module 杂散电感，模块	-	-	35	-	nH
V _{ISOL}	Isolation test voltage 绝缘测试电压	f = 50Hz, t = 30s.		2.5	-	kV
G	Weight 重量	-	-	300	-	g
-	Cree page distance 爬电距离	Terminal to terminal /端子到端子	-	10	-	mm

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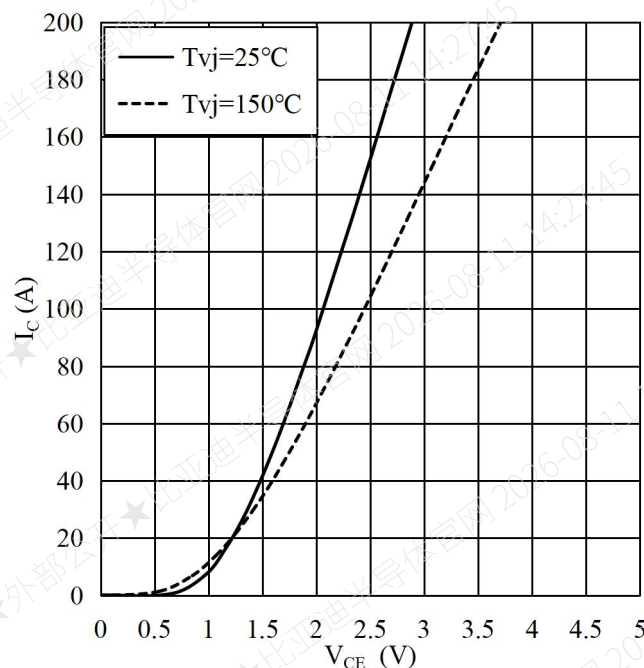
-		Terminal to base /端子到底板	-	10	-	
-	Clearance distance in air 空气间隙	Terminal to terminal /端子到端子	-	7.5	-	
-		Terminal to base /端子到底板	-	7.5	-	
M	Mounting torque for module mounting 模块的安装扭矩	Screw M5 /M5 螺栓	3.0	-	6.0	Nm
-	Internal isolation 内部绝缘	ceramics /陶瓷	Al ₂ O ₃			-
-	Material of module baseplate 模块基板材料	-	Cu			-

Note: The typical reference values in the above parameters are based on laboratory test data under encapsulation conditions and are not to be used as a basis for production test acceptance.

注：以上参数中的典型参考值基于封装条件下实验室测试数据得出，不作为生产测试验收依据。

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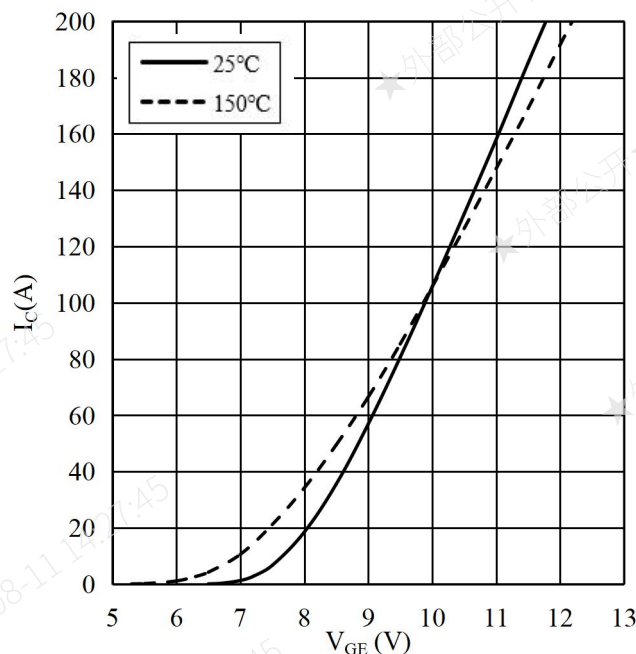
□ Characteristics Diagrams/特性曲线



$$I_C = f(V_{CE}), V_{GE} = 15V$$

Fig.1 Typ. Output Characteristics-Inverter

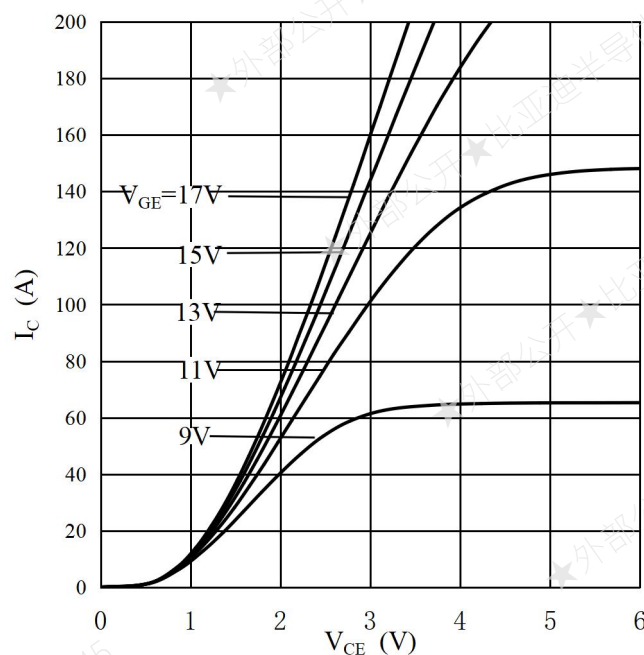
图 1 输出特性-逆变器



$$I_C = f(V_{GE}), V_{CE} = 20V$$

Fig.2 Typ. Transfer Characteristics-Inverter

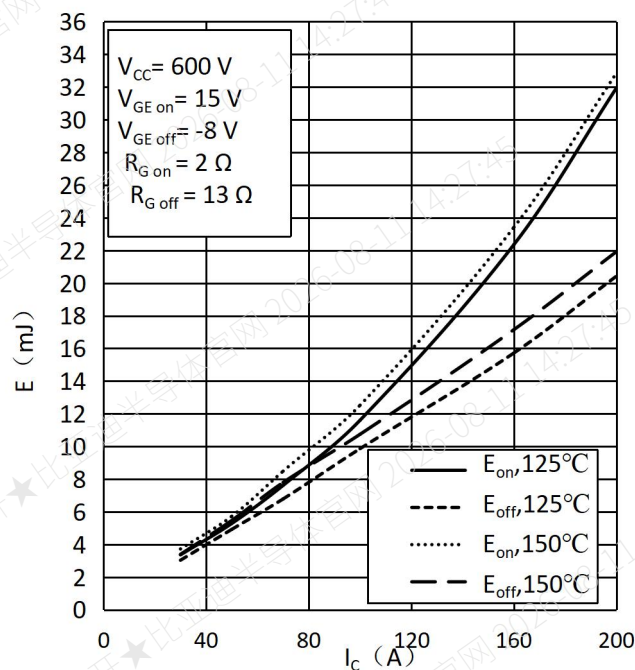
图 2 传输特性-逆变器



$$I_C = f(V_{CE}), T_{vj} = 150^\circ C$$

Fig.3 Typ. Output Characteristics-Inverter

图 3 输出特性-逆变器



$$E_{on} = f(I_C), E_{off} = f(I_C)$$

Fig.4 Switching Loss vs. Collector Current-Inverter

图 4 开关损耗和集电极电流-逆变器

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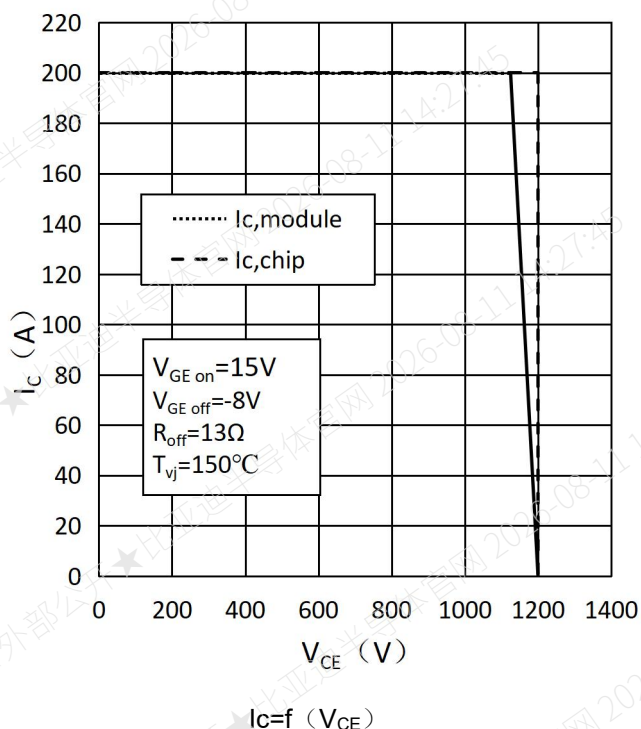


Fig.5 Reverse Bias Safe Operating Area (RBSOA)

-Inverter

图 5 反偏安全工作区-逆变器

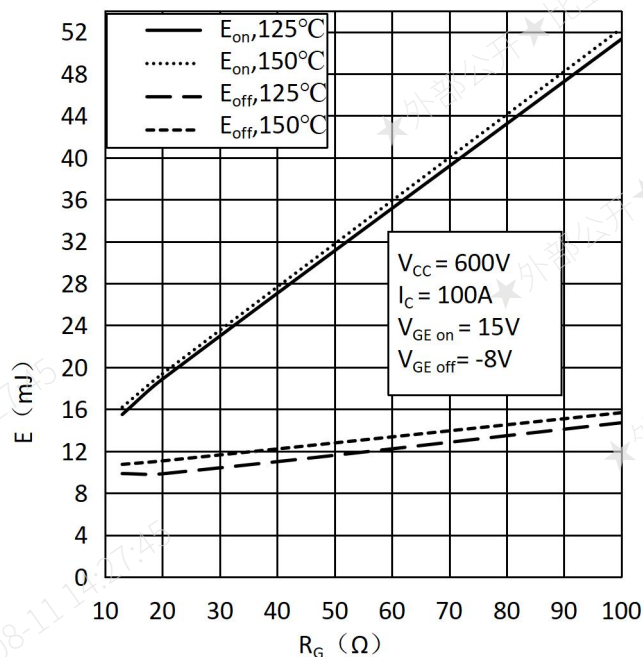


Fig.6 Switching Loss of IGBT vs. Gate Resistor -

Inverter

图 6 IGBT 开关损耗和门极电阻-逆变器

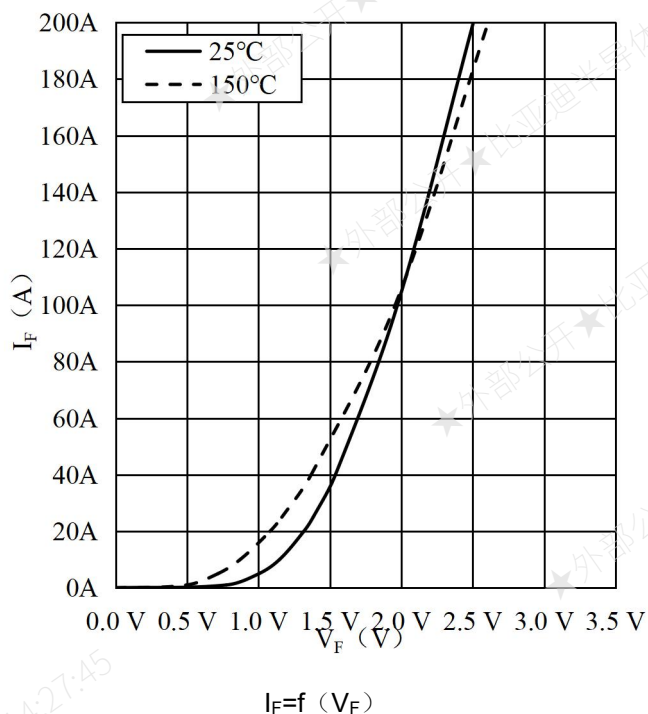


Fig.7 Typ. Forward Characteristics of Diode-Inverter

图 7 二极管正向偏压特性-逆变器

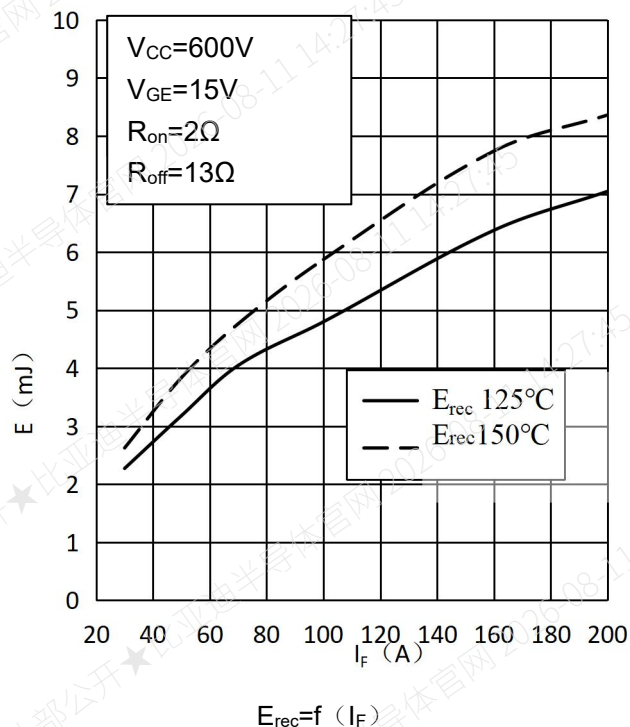
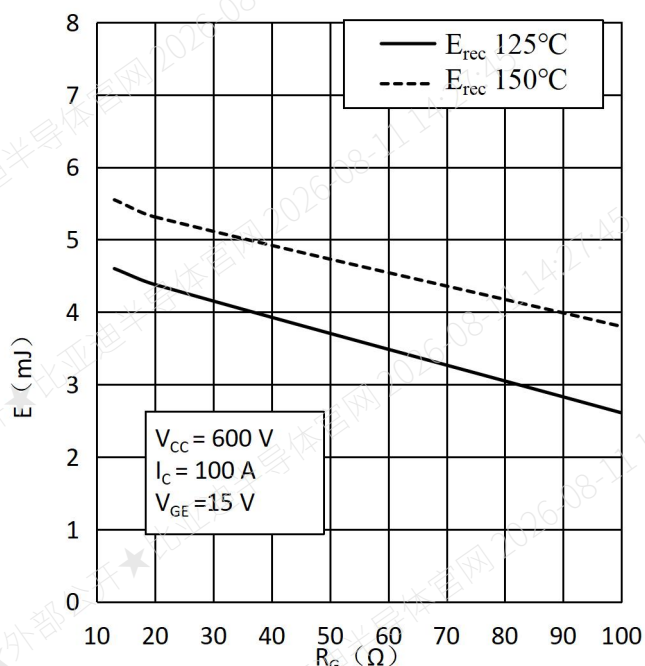


Fig.8 Typ. Switching Losses of Diode-Inverter

图 8 二极管开关损耗-逆变器

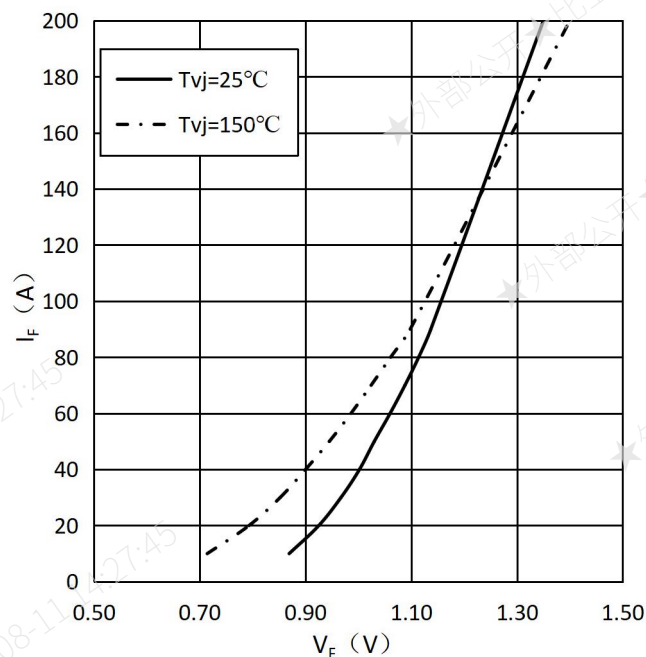
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$$E_{\text{rec}} = f(R_G)$$

Fig.9 Switching Loss of Diode vs. Gate Resistor
-Inverter

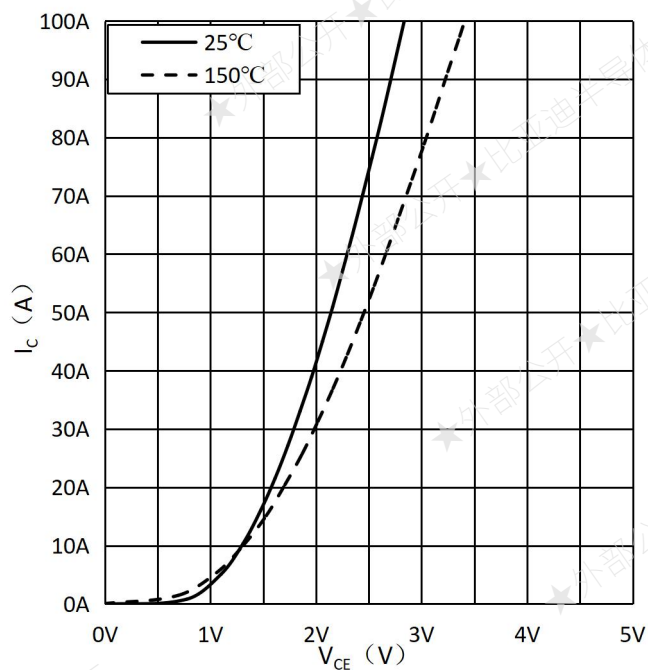
图 9 FRD 开关损耗和门极电阻-逆变器



$$I_F = f(V_F)$$

Fig.10 Forward Characteristics of Diode-Rectifier

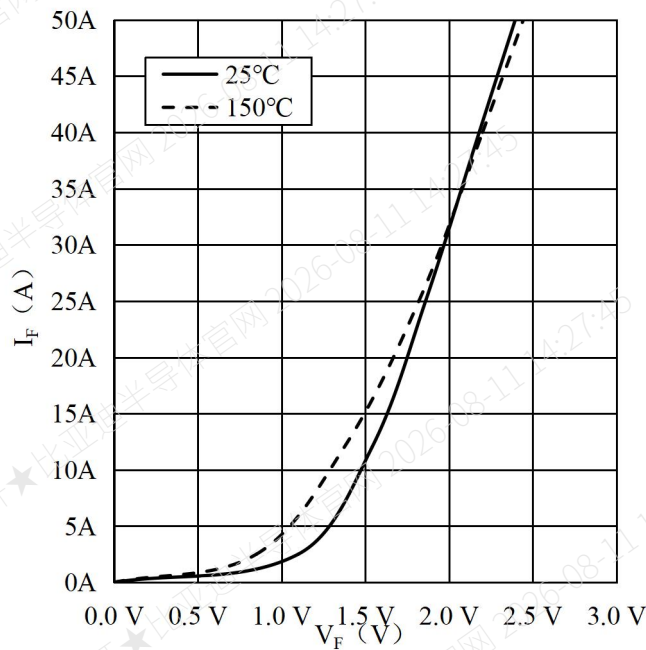
图 10 二极管正向偏压特性-整流器



$$I_C = f(V_{CE}), V_{GE} = 15V$$

Fig.11 Typ. Output Characteristics, Brake-Chopper

图 11 输出特性, 制动-斩波器



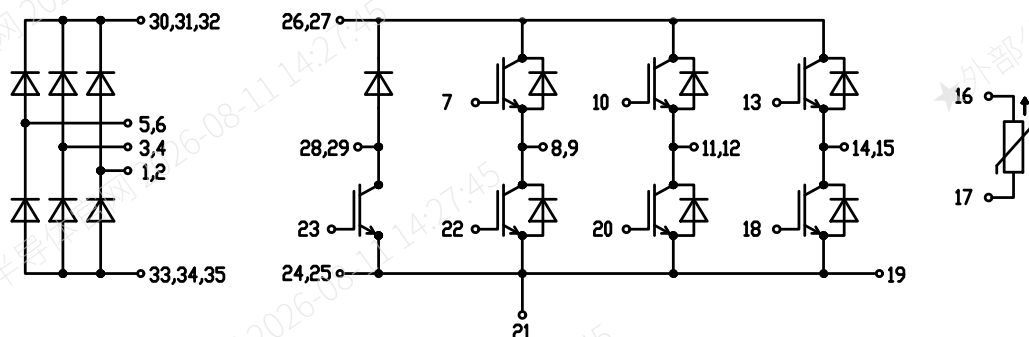
$$I_F = f(V_F)$$

Fig.12 Forward Characteristics of Diode-
Brake-Chopper

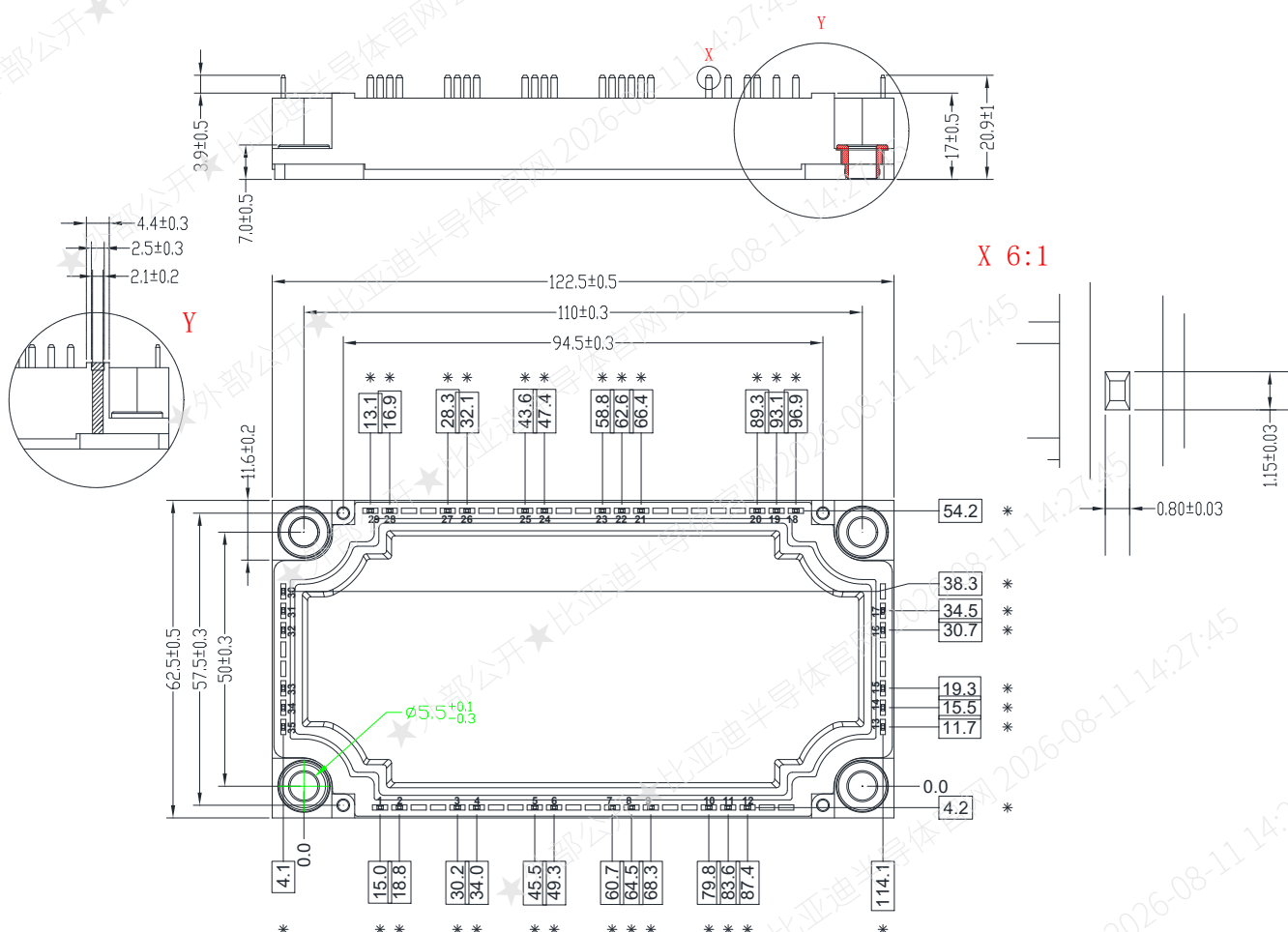
图 12 二极管正向偏压特性, 制动-斩波器

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● Circuit Diagram/接线图



□ Package outlines/封装尺寸



所有带*尺寸为重点尺寸 ± 0.3

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- **Applications:** This product is suitable for industrial electrical applications (including but not limited to: industrial motor drives, frequency converters, UPS, photovoltaic inverters, energy storage converters, industrial welding equipment, power quality devices (SVG, APF), etc.)

使用范围: 本产品适用于工业级电气应用 (包括但不限于: 工业电机驱动、变频器、不间断电源 (UPS)、光伏逆变器、储能变流器、工业焊接设备、电能质量设备 (如 SVG、APF) 等)

- **Warranty Period:** Unless otherwise agreed in the COOPERATION AGREEMENT Or Other WRITTEN DOCUMENTS, The warranty period for the product described in this specification is 12 months from the date of shipment.

质保期: 除双方在合作协议或其他书面文件中另行约定外, 本规格书所述产品质保期自出货起 12 个月。

- **Special Instructions:**

特别说明:

- **Correct and Safety Use of Power Module:** Unsuitable operation (such as electrical, mechanical stress and so on) may lead to damage of power modules. Please pay attention to the following descriptions and use this product according to the guidance.

功率模块安全正确的使用方法: 不当的操作 (如电应力、机械应力等) 可能导致模块损毁。请注意以下介绍, 并根据指导来使用本产品。

- **During Transit:** Tossing or dropping of a carton may damage devices inside. Devices exposed to moisture may result in failure. Special care should be taken during rainy or snowy weather to implement protective measures preventing the device from getting wet.

运输过程中: 包装箱颠簸或坠落可能导致内部器件损毁; 器件遇水受潮将导致故障失效。在雨雪天气尤其要注意保护器件防止淋湿。

- **Storage:** The temperature and humidity of the storage place should be $20\pm 5^{\circ}\text{C}$ and $30\% \sim 60\%\text{RH}$ respectively. The performance and reliability of devices may be jeopardized if devices are stored in an environment far above or below the range indicated above.

贮存: 贮存地点温度与湿度应分别控制在 $20\pm 5^{\circ}\text{C}$ 和 $30\% \sim 60\%\text{RH}$ 。如果贮存环境远高于或低于指示的变化范围, 将危害器件的性能与可靠性。

- **Prolonged Storage:** When storing devices more than one year, dehumidifying measures should be provided for the storage place. When using devices after a long period of storage, please inspect them to ensure there are no scratches, dust, rust, or other defects on the surface.

长期贮存: 当存储器件时间超过一年, 贮存地点应当采取去湿措施。器件经过长期存放使用时, 检查器件确保外观没有刮伤, 灰尘, 锈迹等。

- **Operating Environment:** Devices should not be exposed to water, organic solvents, corrosive gases, explosive gases, fine particles, or corrosive agents, since any of those can lead to a serious accident.

应用环境: 器件不应当暴露在水, 有机溶剂, 腐蚀性气体、易燃易爆性气体, 微尘, 腐蚀性药剂中, 上

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述任何一种情况都会导致严重事故。

- **Anti-electrostatic Measures:** Following precautions should be taken for gated devices to prevent static buildup which could damage the devices:

防静电措施: 带栅极器件应采取以下预警来防止可以损毁器件的静电生成:

1. Static electricity of human bodies and cartons and/or excessive voltage applied across the gate to emitter may damage and rupture devices. Sense-emitter and temperature-sensor are also vulnerable to excessive voltage. The basis of anti-electrostatic is suppression of build-up and quick dissipation of the charged electricity.

1. 门极与发射极间产生的人体静电、包装箱静电和过电压将损毁或击穿器件。采样发射极和温度传感器同样容易受到过压损毁。防静电底板可以抑制电荷生成并快速耗散。

2. Containers that are susceptible to static electricity should not be used for transit or for storage.

2. 不要用易受静电影响的容器运输或贮存器件。

3. Signal terminals to emitter should be always shorted with a carbon cloth or the like until right before a module is used. Never touch the signal terminals with bare hands.

3. 发射极信号端子应一直用碳纤维布或类似物短接直到模块使用前。任何情况下不要徒手碰触信号端子。

4. During the installation process, it is necessary to always maintain the equipment and the operator's body in contact with the ground after removing carbon fiber cloth or similar materials. It is advisable to cover the workstation and its surrounding floor with conductive mats and ground them.

4. 安装过程中始终保持设备和操作人员的身体接触地面（移除碳纤维布或类似物后）。用导电垫覆盖工作地点及周围地板并使其接地。

5. Use soldering irons with grounded tips.

5. 使用接地的烙铁头。

- Our Company is committed to enhancing product quality and stability. This specification serves solely to delineate technical product details.

本公司致力于提高产品质量与稳定性。本文件之目的，仅在于陈述产品相关技术信息。

- **Notwithstanding the Company's reasonable efforts and due diligence, the sensitive nature of the products and variations in testing environments and systems may result in a certain failure rate, including potential malfunctions or failures under specific conditions. Consequently, the Company does not warrant the accuracy of the information contained in this specification, nor the fitness for a particular purpose or merchantability of the products. The information in this specification shall not be construed as a guarantee or commitment regarding product functionality, condition, or quality.**

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- The Company shall not be held liable for any product damage or consequential incidents resulting from usage beyond the recommended storage conditions, operating parameters, or absolute maximum ratings (or other explicitly stated limits) specified in this specification. Customers must strictly adhere to the operational procedures and conditions outlined in the latest version of the specification when utilizing or testing the product. Customers are responsible for complying with safety standards, including but not limited to redundant design, fire prevention measures, and fault prevention, to design and maintain a safe and stable system environment. Customers must verify all functionalities described in this specification before or during actual application to ensure product suitability, safety (preventing potential accidents, fires, or public harm etc.), and reliability. It is recommended that Customers consult our company prior to testing to confirm whether the product information adequately covers the application requirements.

任何超出本文件中建议存储条件、使用条件及绝对最大额定参数条件（或部分明确值）使用，造成的产品损坏或连带事故发生，本公司不承担相关责任。当客户在使用产品时，应根据最新版本文件上规定的操作步骤或示明条件进行使用或测试。客户有责任遵从安全规则（包括冗余设计、防火措施、故障预防等）设计安全及稳定的系统环境，在实际应用前、或实际应用中验证本文件所述的任何功能，以确保适用性、安全性（预防可能发生的任何事故、火灾或社会伤害等）及可靠性。建议客户在测试前可咨询本公司，以验证产品信息是否可以涵盖应用需求。

- This product shall not be used in any equipment or applications requiring higher reliability or quality standards where failure could result in personal injury, death, or catastrophic events, including but not limited to nuclear control systems, aircraft/aviation components, maritime/rail transport equipment, traffic signaling devices, combustion control systems, medical equipment, or other safety-critical applications. Customers must procure genuine products exclusively through the Company or authorized channels, and utilize them strictly within legally permitted boundaries and under conditions expressly defined in this specification. The Company disclaims all liability for losses, damages, or injuries arising from non-compliance with these requirements.

本产品不能且禁止应用在一些需要更高稳定性及质量的特殊设备上，以免导致人员伤亡等意外发生，包括

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原子能控制设备，飞机及航空器件，船舶、轨道等运输设备，交通信号设备，燃烧控制设备，医药设备以及所有安全性设备等。客户应通过本公司或经本公司授权的渠道购买正品，并应在法律约束范围内及本文件明确条件下合法、合理使用，否则造成损失与伤害的，本公司概不负责。

- The information presented in this specification constitutes the latest product details compiled and recorded by our Company with reasonable efforts at the time of publication. To ensure greater accuracy, our Company reserves the right to make periodic corrections, modifications, and version updates to this specification without prior notice. Customers should always refer to the latest version when using or consulting this document.

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